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Jameco Part Number 243731

MC74HC132A

Quad 2-Input NAND Gate with Schmitt-Trigger Inputs

High–Performance Silicon–Gate CMOS

The MC74HC132A is identical in pinout to the LS132. The device inputs are compatible with standard CMOS outputs; with pull–up resistors, they are compatible with LSTTL outputs.

The HC132A can be used to enhance noise immunity or to square up slowly changing waveforms.

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 72 FETs or 18 Equivalent Gates

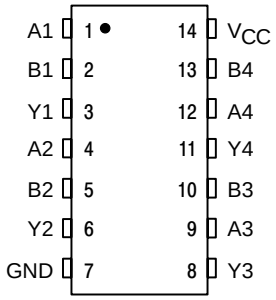

Figure 1. Pin Assignment

FUNCTION TABLE

Inputs		Output
A	B	Y
L	L	H
L	H	H
H	L	H
H	H	L

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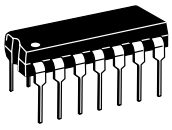
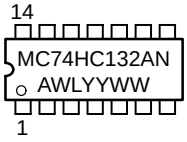
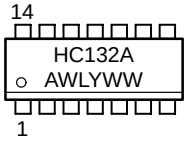
MARKING DIAGRAMS

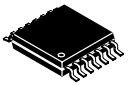


PDIP–14
N SUFFIX
CASE 646

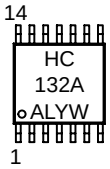


SOIC–14
D SUFFIX
CASE 751A





TSSOP–14
DT SUFFIX
CASE 948G



A = Assembly Location
L, WL = Wafer Lot
Y, YY = Year
W, WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping
MC74HC132AN	PDIP–14	2000/Box
MC74HC132AD	SOIC–14	55/Rail
MC74HC132ADR2	SOIC–14	2500/Reel
MC74HC132ADT	TSSOP–14	96/Rail
MC74HC132ADTR2	TSSOP–14	2500/Reel

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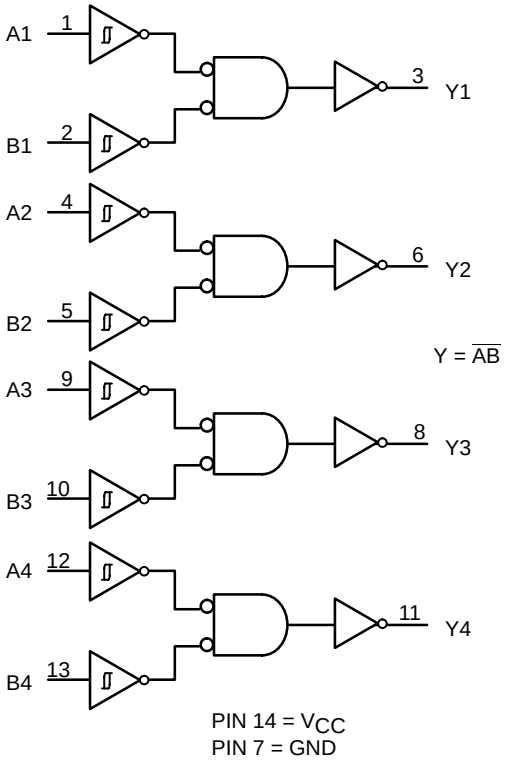


Figure 2. Logic Diagram

MAXIMUM RATINGS (Note 1)

Symbol	Parameter		Value	Unit
V_{CC}	Positive DC Supply Voltage		−0.5 to +7.0	V
V_{IN}	Digital Input Voltage		−0.5 to +7.0	V
V_{OUT}	DC Output Voltage	Output in 3–State High or Low State	−0.5 to +7.0 −0.5 to V_{CC} +0.5	V
I_{IK}	Input Diode Current		−20	mA
I_{OK}	Output Diode Current		±20	mA
I_{OUT}	DC Output Current, per Pin		±25	mA
I_{CC}	DC Supply Current, V_{CC} and GND Pins		±75	mA
I_{GND}	DC Ground Current per Ground Pin		±75	mA
T_{STG}	Storage Temperature Range		−65 to +150	°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds		260	°C
T_J	Junction Temperature Under Bias		+150	°C
θ_{JA}	Thermal Resistance	14–PDIP 14–SOIC 14–TSSOP	78 125 170	°C/W
P_D	Power Dissipation in Still Air at 85°C	PDIP SOIC TSSOP	750 500 450	mW
MSL	Moisture Sensitivity		Level 1	
F_R	Flammability Rating	Oxygen Index: 30% – 35%	UL–94–VO (0.125 in)	
V_{ESD}	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	>2000 >100 >500	V
$I_{Latch–Up}$	Latch–Up Performance	Above V_{CC} and Below GND at 85°C (Note 5)	±300	mA

1. Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Extended exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute maximum–rated conditions is not implied.
2. Tested to EIA/JESD22–A114–A.
3. Tested to EIA/JESD22–A115–A.
4. Tested to JESD22–C101–A.
5. Tested to EIA/JESD78.
6. For high frequency or heavy load considerations, see Chapter 2the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)	2.0	6.0	V
V_{IN}, V_{OUT}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V_{CC}	V
T_A	Operating Temperature, All Package Types	−55	+125	°C
t_r, t_f	Input Rise and Fall Time (Figure 3)	–	No Limit (Note 7)	ns

7. When $V_{IN} \sim 0.5\ V_{CC}$, I_{CC} >> quiescent current.
8. Unused inputs may not be left open. All inputs must be tied to a high–logic voltage level or a low–logic input voltage level.

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V_{CC} V	Guaranteed Limit			Unit
				−55°C to 25°C	≤85°C	≤125°C	
V_{T+}max	Maximum Positive–Going Input Threshold Voltage (Figure 5)	V_{OUT} = 0.1 V $\|I_{OUT}\| \le 20$ μA	2.0 4.5 6.0	1.5 3.15 4.2	1.5 3.15 4.2	1.5 3.15 4.2	V
V_{T+}min	Minimum Positive–Going Input Threshold Voltage (Figure 5)	V_{OUT} = 0.1 V $\|I_{OUT}\| \le 20$ μA	2.0 4.5 6.0	1.0 2.3 3.0	0.95 2.25 2.95	0.95 2.25 2.95	V
V_{T-}max	Maximum Negative–Going Input Threshold Voltage (Figure 5)	$V_{OUT} = V_{CC}$ – 0.1 V $\|I_{OUT}\| \le 20$ μA	2.0 4.5 6.0	0.9 2.0 2.6	0.95 2.05 2.65	0.95 2.05 2.65	V
V_{T-}min	Minimum Negative–Going Input Threshold Voltage (Figure 5)	$V_{OUT} = V_{CC}$ – 0.1 V $\|I_{OUT}\| \le 20$ μA	2.0 4.5 6.0	0.3 0.9 1.2	0.3 0.9 1.2	0.3 0.9 1.2	V
$V_H$max (Note 9)	Maximum Hysteresis Voltage (Figure 5)	V_{OUT} = 0.1 V or V_{CC} – 0.1 V $\|I_{OUT}\| \le 20$ μA	2.0 4.5 6.0	1.2 2.25 3.0	1.2 2.25 3.0	1.2 2.25 3.0	V
$V_H$min (Note 9)	Minimum Hysteresis Voltage (Figure 5)	V_{OUT} = 0.1 V or V_{CC} – 0.1 V $\|I_{OUT}\| \le 20$ μA	2.0 4.5 6.0	0.2 0.4 0.5	0.2 0.4 0.5	0.2 0.4 0.5	V
V_{OH}	Minimum High–Level Output Voltage	$V_{IN} \le V_{T-}$min or V_{T+}max $\|I_{OUT}\| \le 20$ μA	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$V_{IN} \le -V_{T-}$min or V_{T+}max $\|I_{OUT}\| \le 4.0$ mA $\|I_{OUT}\| \le 5.2$ mA	 4.5 6.0	 3.98 5.48	 3.84 5.34	 3.7 5.2	V
V_{OL}	Maximum Low–Level Output Voltage	$V_{IN} \ge V_{T+}$max $\|I_{OUT}\| \le 20$ μA	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$V_{IN} \ge V_{T+}$max $\|I_{OUT}\| \le 4.0$ mA $\|I_{OUT}\| \le 5.2$ mA	4.5 6.0	0.26 0.26	0.33 0.33	0.4 0.4	V
I_{IN}	Maximum Input Leakage Current	$V_{IN} = V_{CC}$ or GND	6.0	±0.1	±1.0	±1.0	μA
I_{CC}	Maximum Quiescent Supply Current (per Package)	$V_{IN} = V_{CC}$ or GND I_{OUT} = 0 μA	6.0	1.0	10	40	μA

9. $V_H$min > (V_{T+}min) − (V_{T-}max); $V_H$max = (V_{T+}max) + (V_{T-}min).
10. Information on typical parametric values can be found in the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input $t_r = t_f$ = 6.0 ns)

Symbol	Parameter	V_{CC} V	Guaranteed Limit −55°C to 25°C	Guaranteed Limit ≤85°C	Guaranteed Limit ≤125°C	Unit
t_{PLH}, t_{PHL}	Maximum Propagation Delay, Input A or B to Output Y (Figures 3 and 4)	2.0 4.5 6.0	125 25 21	155 31 26	190 38 32	ns
t_{TLH}, t_{THL}	Maximum Output Transition Time, Any Output (Figures 3 and 4)	2.0 4.5 6.0	75 15 13	95 19 16	110 22 19	ns
C_{in}	Maximum Input Capacitance	—	10	10	10	pF

11. For propagation delays with loads other than 50 pF, and information on typical parametric values, see the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

		Typical @ 25°C, V_{CC} = 5.0 V	
C_{PD}	Power Dissipation Capacitance (per Gate) (Note 12)	24	pF

12. Used to determine the no–load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$. For load considerations, see the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

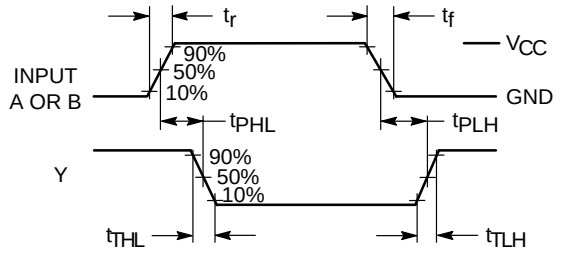
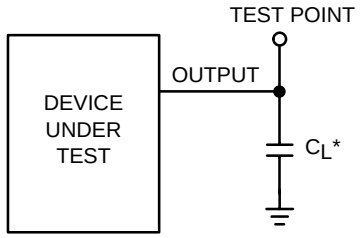


Figure 3. Switching Waveforms



*Includes all probe and jig capacitance

Figure 4. Test Circuit

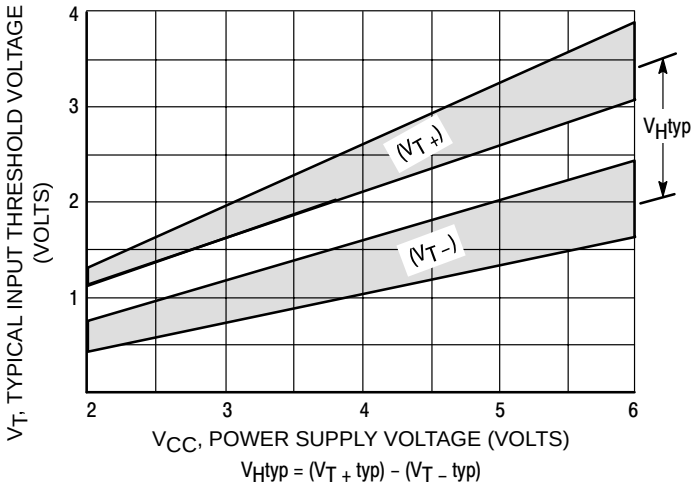


Figure 5. Typical Input Threshold, V_{T+}, V_{T-} Versus Power Supply Voltage

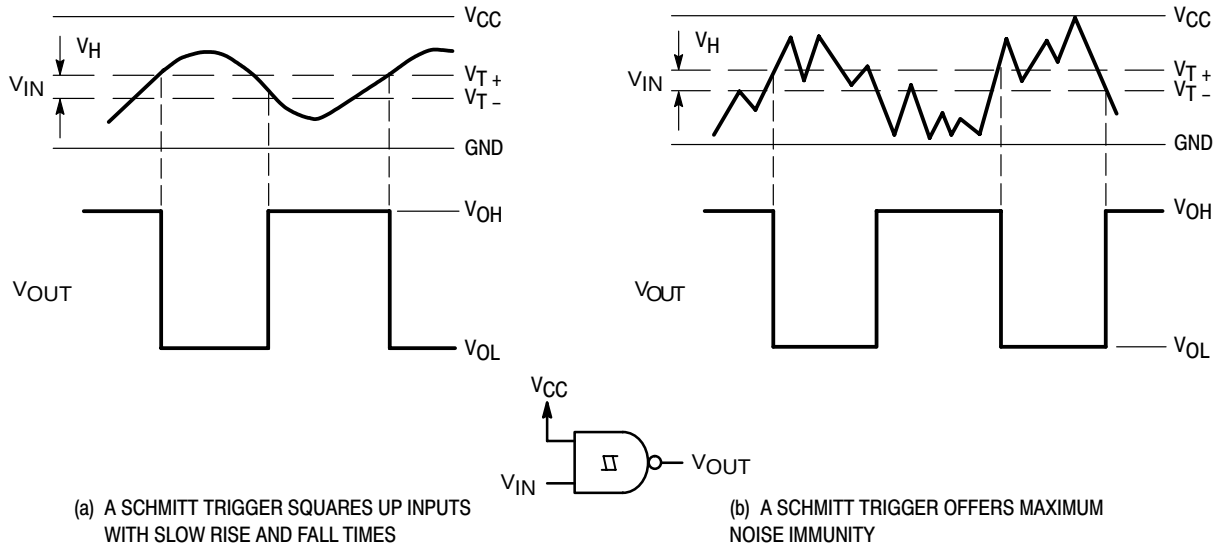
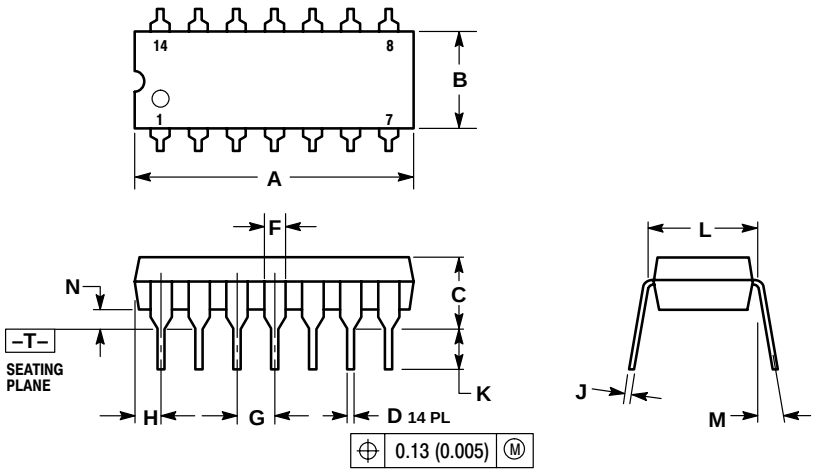


Figure 6. Typical Schmitt–Trigger Applications

PACKAGE DIMENSIONS

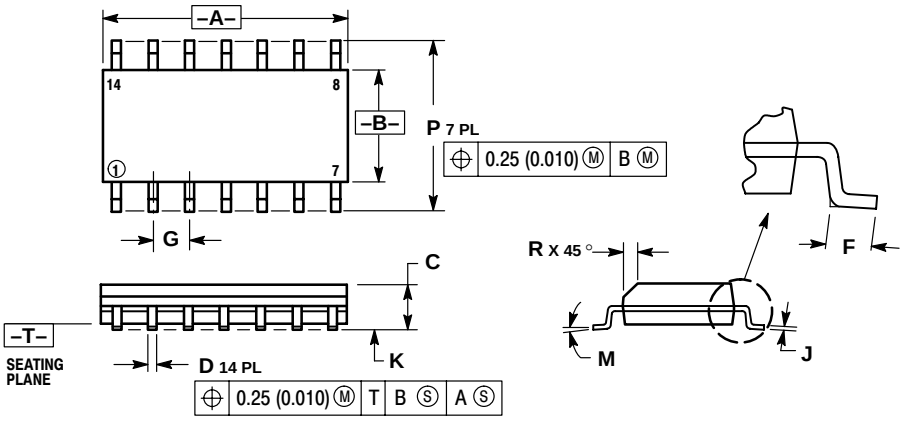
PDIP–14
N SUFFIX
CASE 646–06
ISSUE M



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
5. ROUNDED CORNERS OPTIONAL.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.715	0.770	18.16	18.80
B	0.240	0.260	6.10	6.60
C	0.145	0.185	3.69	4.69
D	0.015	0.021	0.38	0.53
F	0.040	0.070	1.02	1.78
G	0.100 BSC		2.54 BSC	
H	0.052	0.095	1.32	2.41
J	0.008	0.015	0.20	0.38
K	0.115	0.135	2.92	3.43
L	0.290	0.310	7.37	7.87
M	---	10°	---	10°
N	0.015	0.039	0.38	1.01

SOIC–14
D SUFFIX
CASE 751A–03
ISSUE F

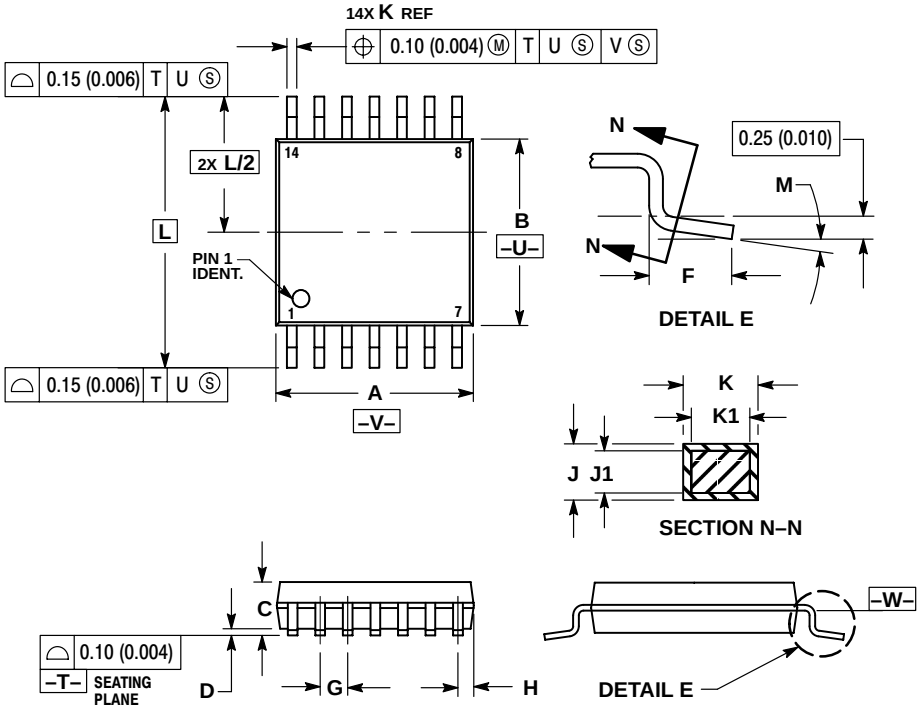


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	8.55	8.75	0.337	0.344
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0 °	7 °	0 °	7 °
P	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

PACKAGE DIMENSIONS

TSSOP–14
DT SUFFIX
CASE 948G–01
ISSUE O



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

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